

1. Scope

The present specifications shall apply to FMXK-1106S.

2. Outline

High Frequency Rectification

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification,etc

3. Flammability

UL94V-0(Equivalent)

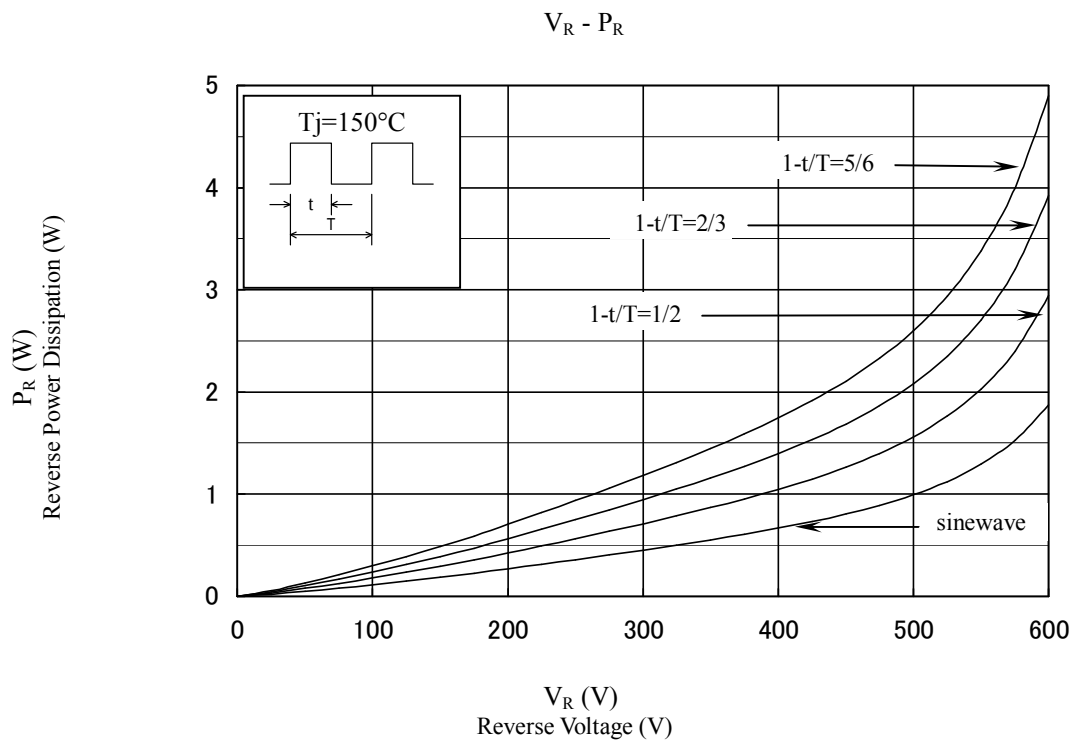
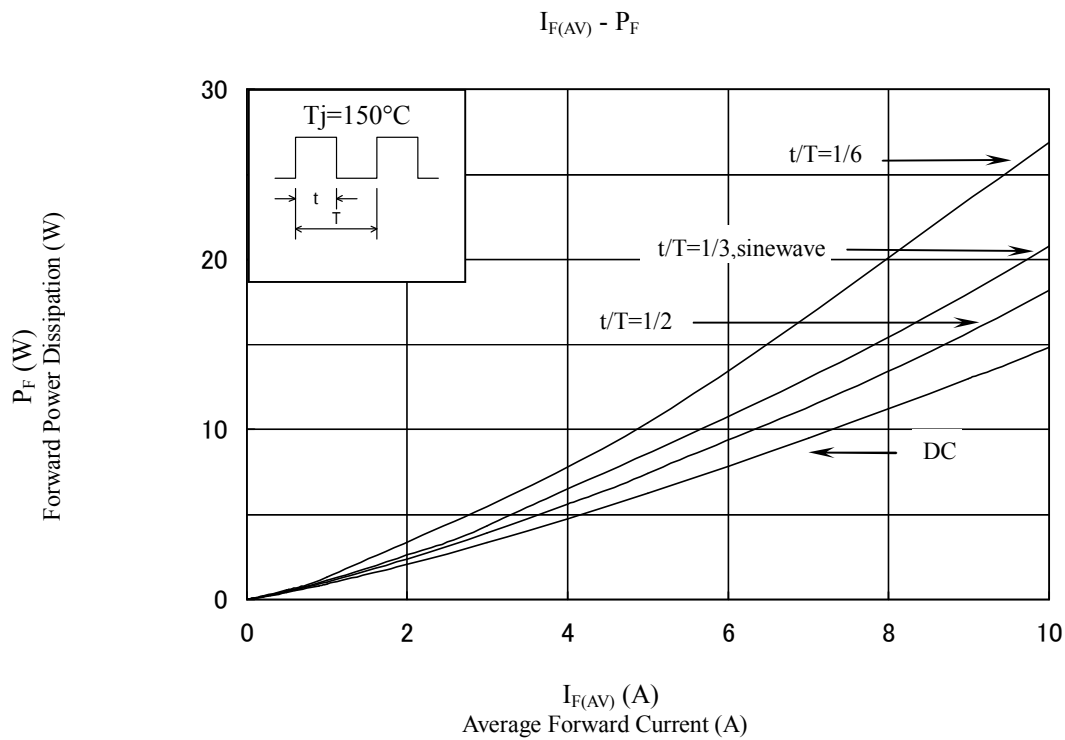
4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	600	
2	Peak Reverse Voltage	V_{RM}	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	10	$T_c=66.8^{\circ}\text{C}$, Sinewave
4	Peak Surge Forward Current	I_{FSM}	A	100	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	50	$1\text{msec} \leq t \leq 10\text{msec}$
6	Junction Temperature	T_j	$^{\circ}\text{C}$	-40~+150	
7	Storage Temperature	T_{stg}	$^{\circ}\text{C}$	-40~+150	

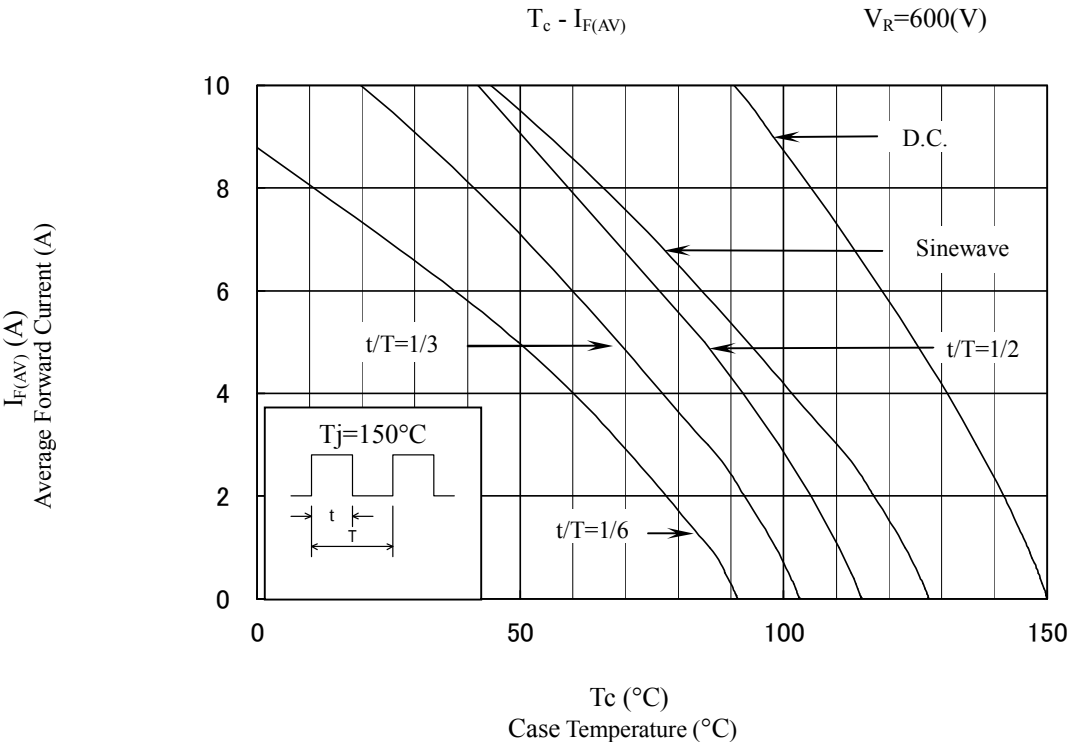
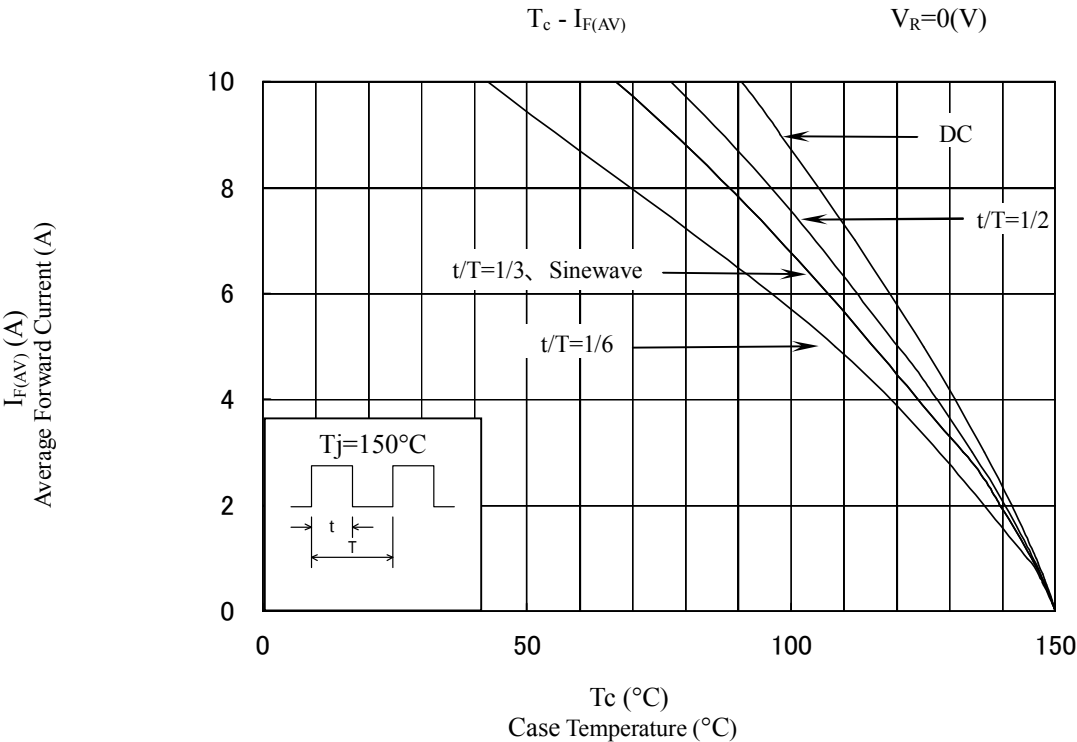
5. Electrical characteristics

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.75 max.	$I_F=10\text{A}$
2	Reverse Leakage Current	I_R	μA	100 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	10 max.	$V_R=V_{RM}$, $T_j=150^{\circ}\text{C}$
4	Reverse Recovery Time	t_{rr}	ns	27 max	$I_F=I_{RP}=500\text{mA}$ 75% Recovery point, $T_j=25^{\circ}\text{C}$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}\text{C}/\text{W}$	4 max.	Between Junction and case

6. Characteristics

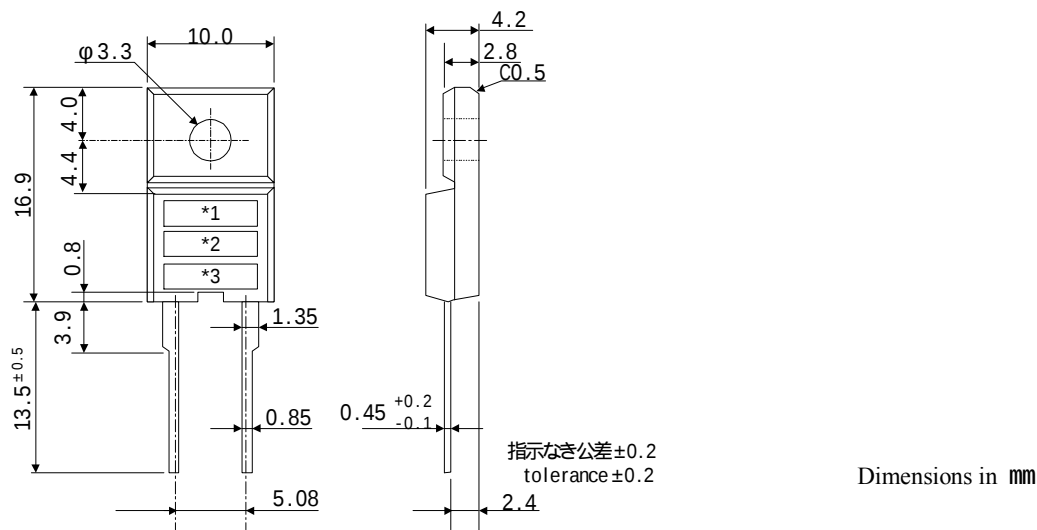


7. Derating



8. Package information

8-1Package type, physical dimensions and material



8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking

Type Name	Marking		
	* 1 Type Name	* 2 Polarity	* 3 Lot number
FMXK-1106S	XK1106	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 5O17 (Oct. 17, 2005)